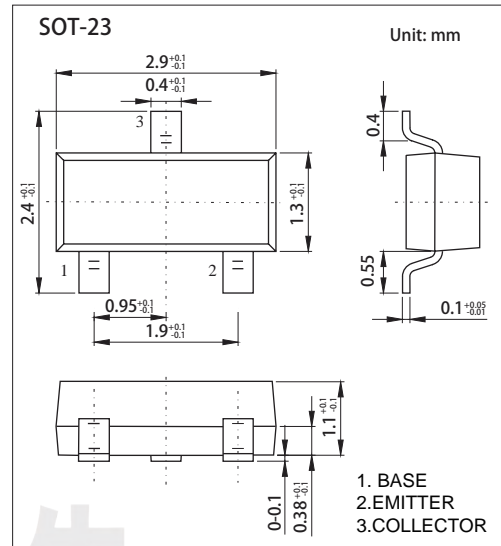


PNP Transistors MMBT5401

■ Features

- Collector current: $I_c = -0.6A$
- Complementary to MMBT5551



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-160	V
Collector - Emitter Voltage	V_{CE0}	-150	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_c	-600	mA
Collector Power Dissipation	P_c	300	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	416	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	

Transistor

PNP Transistors

MMBT5401

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	VCBO	IC= -100 μA, IE=0	-160			V
Collector- emitter breakdown voltage	VCEO	IC= -10 mA, IB=0	-150			
Emitter - base breakdown voltage	VEBO	IE= -10 μA, IC=0	-5			
Collector cut-off current	ICBO	VCE= -120 V, IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB= -4V, IC=0			-0.1	
Collector-emitter saturation voltage	VCE(sat)	IC=-10 mA, IB= -1mA			-0.2	V
		IC=-50 mA, IB= -5mA			-0.5	
Base - emitter saturation voltage	VBE(sat)	IC=-10 mA, IB= -1mA			-1	
		IC=-50 mA, IB= -5mA			-1	
DC current gain	hFE(1)	VCE= -5V, IC= -1mA	80			
	hFE(2)	VCE= -5V, IC= -10mA	100		300	
	hFE(3)	VCE= -5V, IC= -50mA	50			
Transition frequency	fT	VCE= -20V, IC= -10mA, f=100MHz	300			MHz

■ Classification of hFE(2)

Rank	L	H
Range	100-200	200-300
Marking	2L	

Transistor

PNP Transistors MMBT5401

■ Typical Characteristics

